

# Low $V_{CE(sat)}$ Transistor ( $-20V, -3A$ )

## 2SB1424 / 2SA1585S

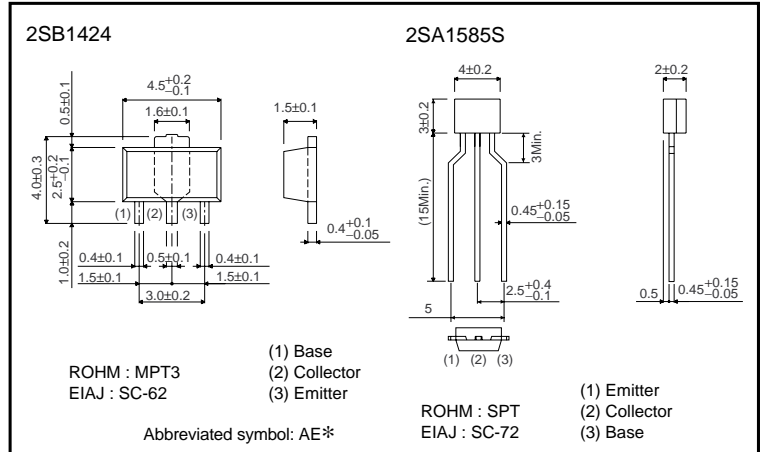
**●Features**

- 1) Low  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = -0.2V$  (Typ.)  
 $(I_C/I_B = -2A / -0.1A)$
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SD2150 / 2SC4115S.

**●Structure**

Epitaxial planar type  
 PNP silicon transistor

**●External dimensions (Unit : mm)**



\* Denotes hFE

**●Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CB0}$	-20	V
Collector-emitter voltage	$V_{CE0}$	-20	V
Emitter-base voltage	$V_{EB0}$	-6	V
Collector current	2SB1424	-3	A
	2SA1585S	-2	
	$I_{CP}$	-5	A(Pulse) *
Collector power dissipation	2SB1424	0.5	W
	2SA1585S	0.4	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to 150	°C

\* Single pulse  $P_w=10ms$

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	-20	-	-	V	I <sub>C</sub> = -50μA
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	-20	-	-	V	I <sub>C</sub> = -1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	-6	-	-	V	I <sub>E</sub> = -50μA
Collector cutoff current	I <sub>CB0</sub>	-	-	-0.1	μA	V <sub>CB</sub> = -20V
Emitter cutoff current	I <sub>EB0</sub>	-	-	-0.1	μA	V <sub>EB</sub> = -5V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	-	-0.5	V	I <sub>C</sub> /I <sub>B</sub> = -2A/ -0.1A
DC current transfer ratio	h <sub>FE</sub>	120	-	390	-	V <sub>CE</sub> = -2V, I <sub>C</sub> = -0.1A
Transition frequency	f <sub>T</sub>	-	240	-	MHz	V <sub>CE</sub> = -2V, I <sub>E</sub> =0.5A, f=100MHz
Output capacitance	C <sub>ob</sub>	-	35	-	pF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0A, f=1MHz

●Packaging specifications and h<sub>FE</sub>

Type	h <sub>FE</sub>	Package	Taping	
		Code	TP	T100
		Basic ordering unit (pieces)	5000	1000
2SA1585S	QR		○	-
2SB1424	QR		-	○

h<sub>FE</sub> values are classified as follows :

Item	Q	R
h <sub>FE</sub>	120 to 270	180 to 390

●Electrical characteristic curves

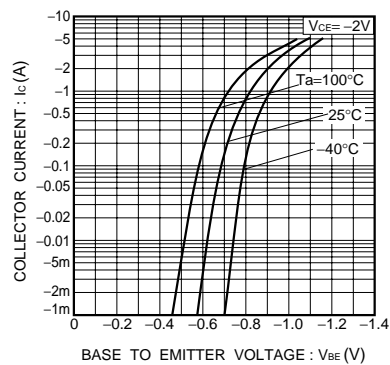


Fig.1 Grounded emitter propagation characteristics

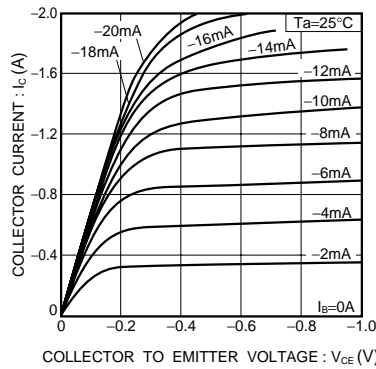


Fig.2 Grounded emitter output characteristics (I)

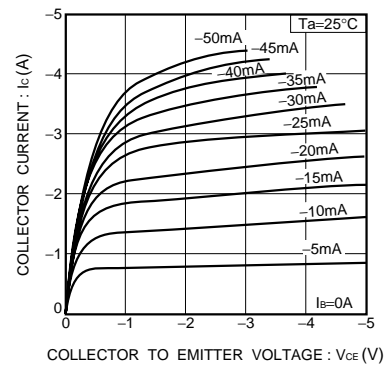


Fig.3 Grounded emitter output characteristics (II)

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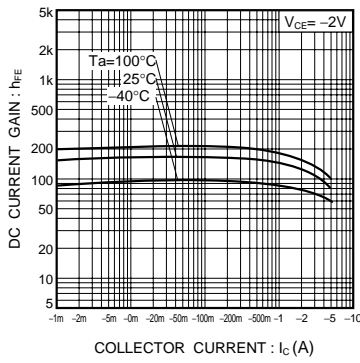


Fig.4 DC current gain vs. collector current

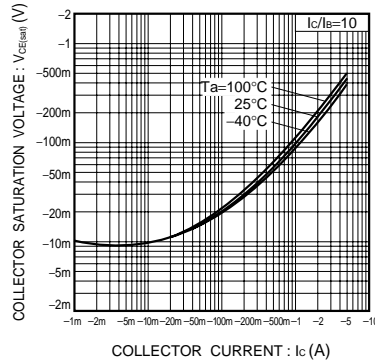


Fig.5 Collector-emitter saturation voltage vs. collector current ( I )

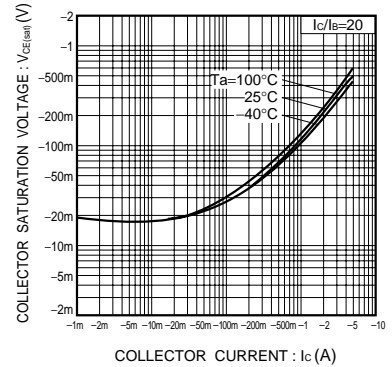


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

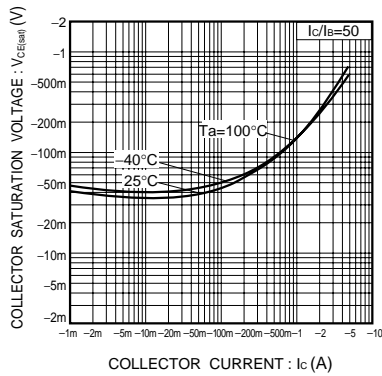


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

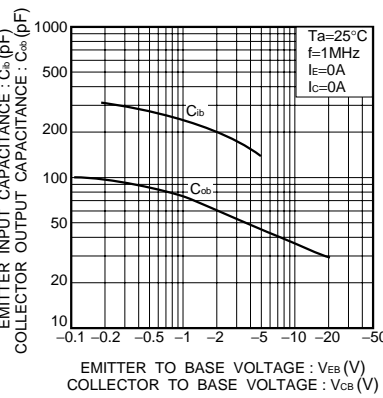


Fig.8 Gain bandwidth product vs. emitter current  
Collector output capacitance vs. collector-base voltage

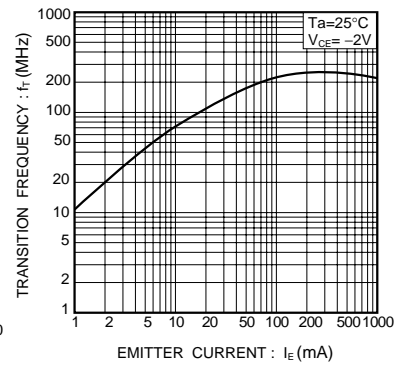


Fig.9 Emitter input capacitance vs. emitter base voltage

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